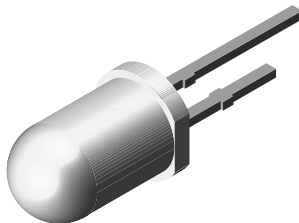


Infrared Emitting Diode, 875 nm, GaAlAs



94 8390

FEATURES

- Package type: leaded
- Package form: T-1 3/4
- Dimensions (in mm): $\varnothing$ 5
- Leads with stand-off
- Peak wavelength: $\lambda_p = 875$ nm
- High reliability
- Angle of half intensity: $\phi = \pm 24^\circ$
- Low forward voltage
- Suitable for high pulse current operation
- Good spectral matching with Si photodetectors
- Compliant to RoHS Directive 2002/95/EC and in accordance to WEEE 2002/96/EC



RoHS
COMPLIANT
GREEN
(5-2008)**

DESCRIPTION

The TSHA5500 is an infrared, 875 nm emitting diode in GaAlAs on GaAlAs technology, molded in a clear, untinted plastic package.

Note

** Please see document "Vishay Material Category Policy":
www.vishay.com/doc?99902

APPLICATIONS

- Infrared remote control and free air data transmission systems with comfortable radiation angle
- This emitter is dedicated to systems with panes in transmission space between emitter and detector, because of the low absorption of 875 nm radiation in glass

PRODUCT SUMMARY

COMPONENT	I_e (mW/sr)	ϕ (deg)	λ_p (nm)	t_r (ns)
TSHA5500	30	± 24	875	600

Note

- Test conditions see table "Basic Characteristics"

ORDERING INFORMATION

ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM
TSHA5500	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1 3/4

Note

- MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS ($T_{amb} = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
Reverse voltage		V_R	5	V
Forward current		I_F	100	mA
Peak forward current	$t_p/T = 0.5$, $t_p = 100$ μs	I_{FM}	200	mA
Surge forward current	$t_p = 100$ μs	I_{FSM}	2.5	A
Power dissipation		P_V	180	mW
Junction temperature		T_j	100	$^\circ\text{C}$
Operating temperature range		T_{amb}	- 40 to + 85	$^\circ\text{C}$
Storage temperature range		T_{stg}	- 40 to + 100	$^\circ\text{C}$
Soldering temperature	$t \leq 5$ s, 2 mm from case	T_{sd}	260	$^\circ\text{C}$
Thermal resistance junction/ambient	J-STD-051, leads 7 mm, soldered on PCB	R_{thJA}	230	K/W

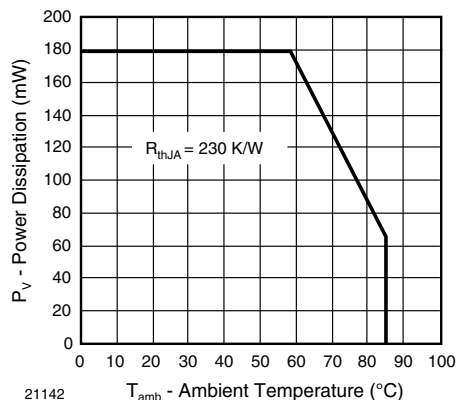


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

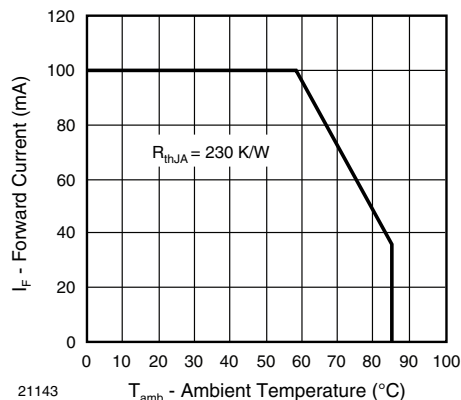


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	$I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$	V_F		1.5	1.8	V
	$I_F = 1\text{ A}$, $t_p = 100\text{ }\mu\text{s}$	V_F		2.8	3.5	V
Temperature coefficient of V_F	$I_F = 100\text{ mA}$	TK_{V_F}		- 1.6		mV/K
Reverse current	$V_R = 5\text{ V}$	I_R			100	μA
Junction capacitance	$V_R = 0\text{ V}$, $f = 1\text{ MHz}$, $E = 0$	C_j		20		pF
Radiant intensity	$I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$	I_e	16	30	48	mW/sr
	$I_F = 1\text{ A}$, $t_p = 100\text{ }\mu\text{s}$	I_e	128	240		mW/sr
Radiant power	$I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$	ϕ_e		24		mW
Temperature coefficient of ϕ_e	$I_F = 20\text{ mA}$	TK_{ϕ_e}		- 0.7		%/K
Angle of half intensity		ϕ		± 24		deg
Peak wavelength	$I_F = 100\text{ mA}$	λ_p		875		nm
Spectral bandwidth	$I_F = 100\text{ mA}$	$\Delta\lambda$		80		nm
Temperature coefficient of λ_p	$I_F = 100\text{ mA}$	TK_{λ_p}		0.2		nm/K
Rise time	$I_F = 100\text{ mA}$	t_r		600		ns
	$I_F = 1\text{ A}$	t_r		300		ns
Fall time	$I_F = 100\text{ mA}$	t_f		600		ns
	$I_F = 1\text{ A}$	t_f		300		ns
Virtual source diameter		d		2.2		mm

BASIC CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified)

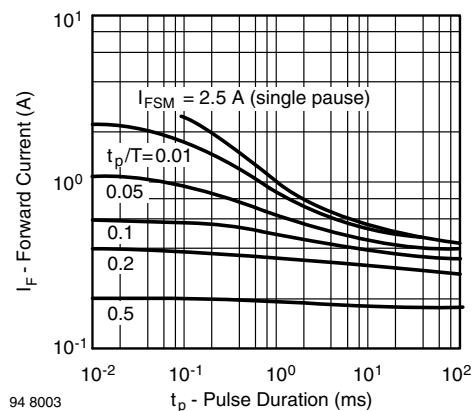


Fig. 3 - Pulse Forward Current vs. Pulse Duration

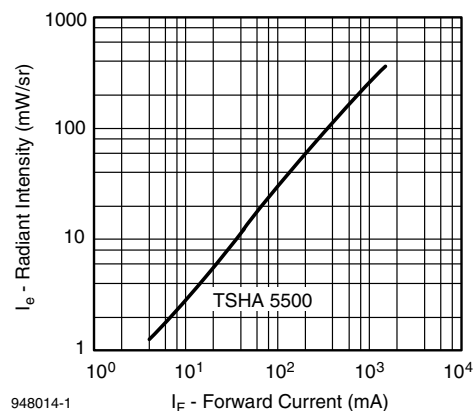


Fig. 6 - Radiant Intensity vs. Forward Current

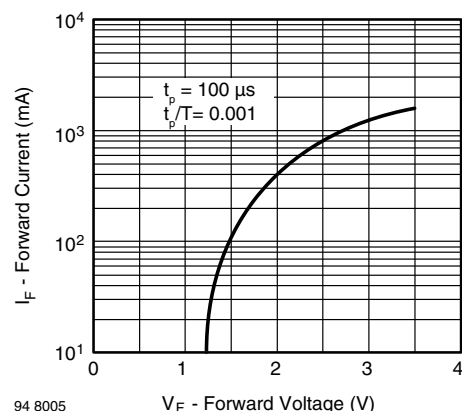


Fig. 4 - Forward Current vs. Forward Voltage

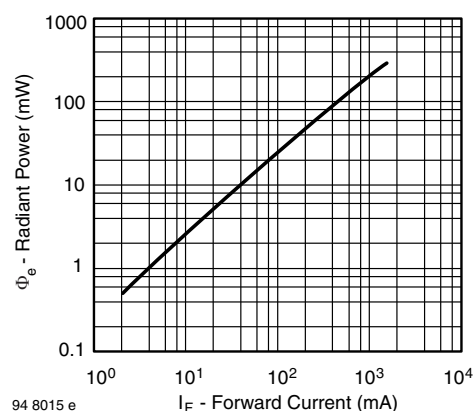


Fig. 7 - Radiant Power vs. Forward Current

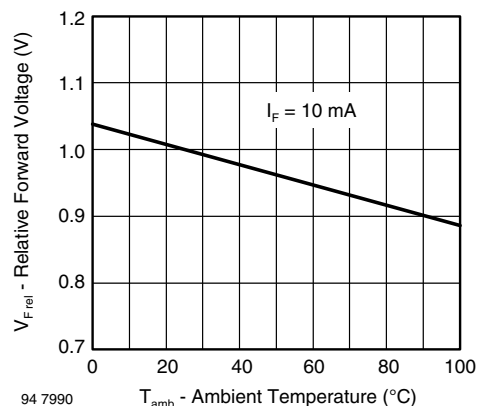


Fig. 5 - Relative Forward Voltage vs. Ambient Temperature

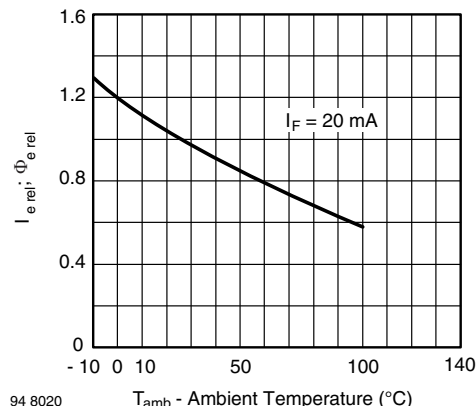


Fig. 8 - Relative Radiant Intensity/Power vs. Ambient Temperature

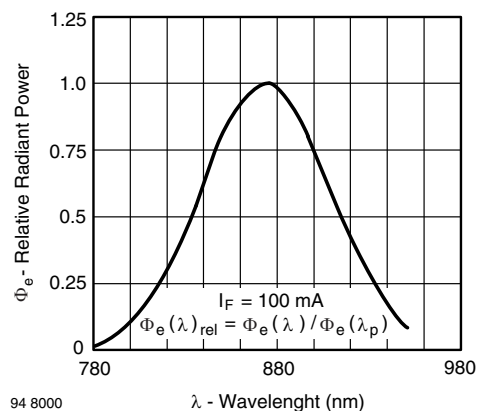


Fig. 9 - Relative Radiant Power vs. Wavelength

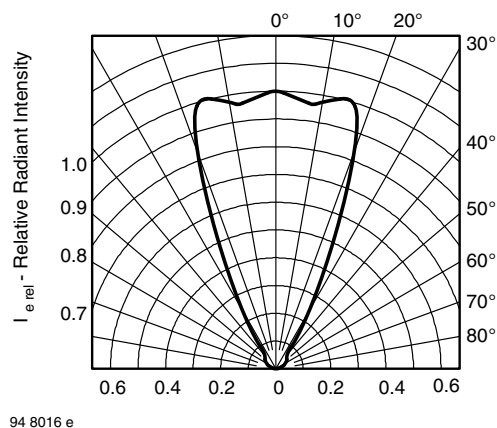
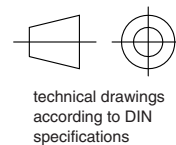
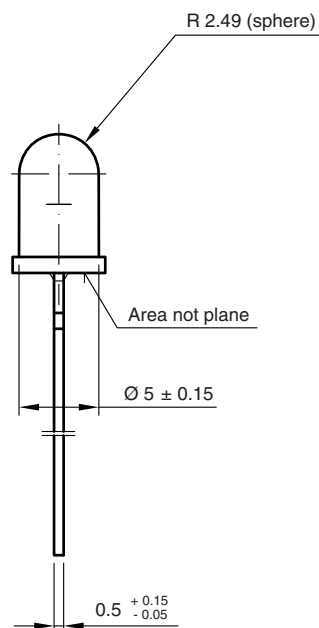
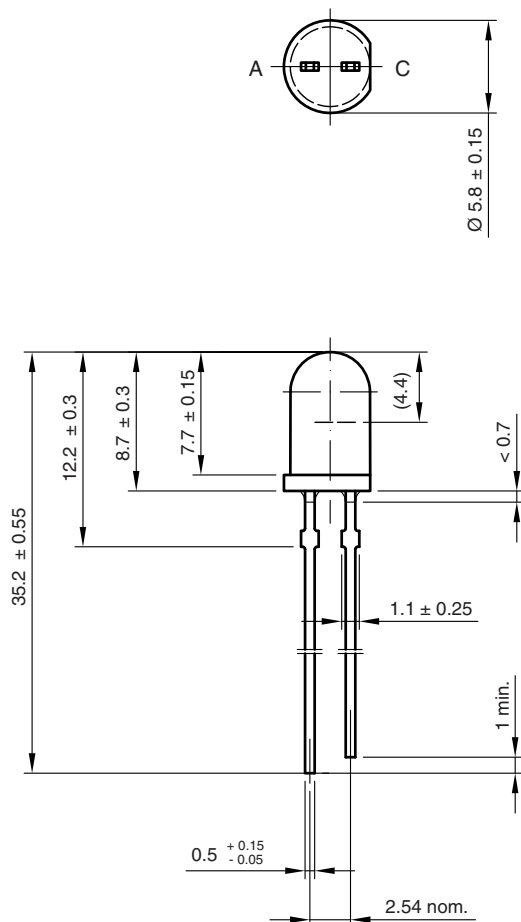


Fig. 10 - Relative Radiant Intensity vs. Angular Displacement

PACKAGE DIMENSIONS in millimeters



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 Issue: 4; 19.05.09
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